

### ● General Description

The AGMH6018C combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

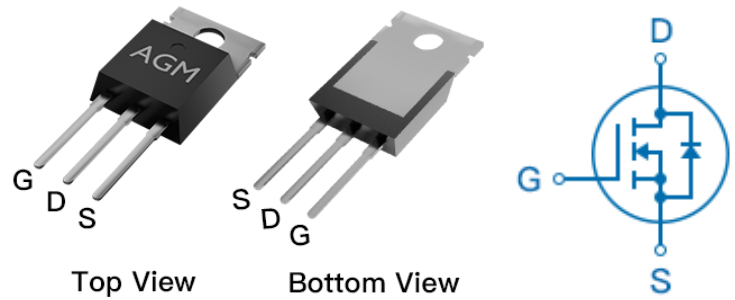
### ● Application

- Electronic Ballast
- Electronic Transformer
- Switch Mode Power Supply

### Product Summary

BVDSS	RDSON	ID
60V	1.9mΩ	150A

### TO-220 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGMH6018C	AGMH6018C	TO-220	---	---	1000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	150	A
	Drain Current-Continuous(Tc=100°C)	102	A
IDM (pluse)	Drain Current-Pulsed <b>(Note 2)</b>	600	A
PD	Maximum Power Dissipation(Tc=25°C)	260	w
	Maximum Power Dissipation(Tc=100°C)	104	w
EAS	Avalanche energy <b>(Note 3)</b>	705	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	0.48	°C/W

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.0	--	4.0	V
gFS	Forward Transconductance	VDS=5V,ID=10A	--	24	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	1.9	2.6	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=30V,VGS=0V, F=1MHZ	--	4525	--	pF
Coss	Output Capacitance		--	1769	--	pF
Crss	Reverse Transfer Capacitance		--	90	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.8	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VDD=30V, VGS=10V, RGEN=2Ω	--	22.5	--	nS
tr	Turn-on Rise Time		--	6.7	--	nS
td(off)	Turn-Off Delay Time		--	80	--	nS
tf	Turn-Off Fall Time		--	27	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=20A	--	65	--	nC
Qgs	Gate-Source Charge		--	12	--	nC
Qgd	Gate-Drain Charge		--	9.8	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	150	A
VSD	Forward on Voltage	VGS=0V,ISD=20A	--	--	1.2	V
trr	Reverse Recovery Time	VDD=20V,IF=20A , dI/dt=100A/μs , TJ=25°C	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: T<sub>J</sub>=25°C,VDD=30V,Vgs=10V,ID=84A,L=0.2mH,RG=25ohm

## ■ Typical Performance Characteristics

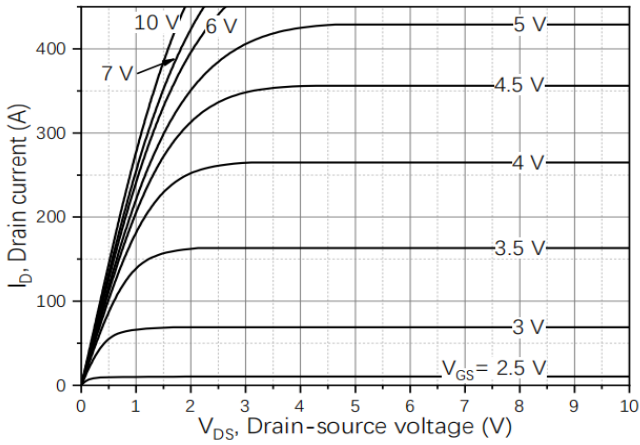


Figure1. Output Characteristics

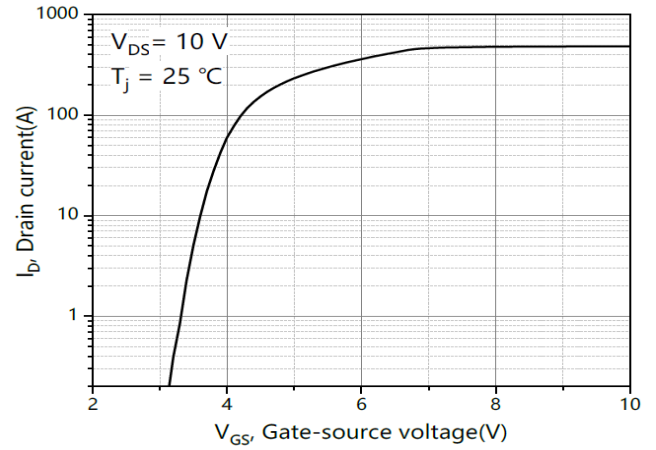


Figure2. Transfer Characteristics

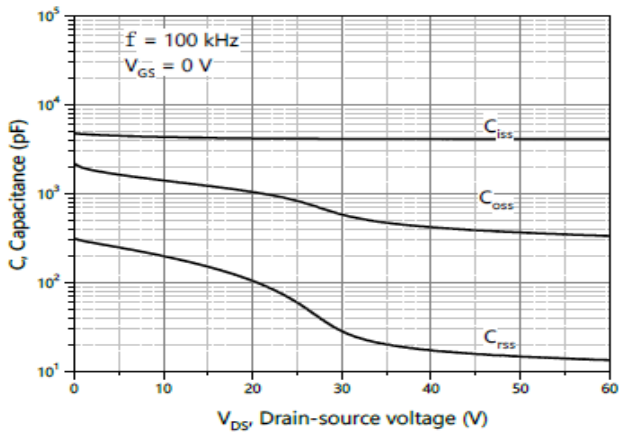


Figure3. Capacitance Characteristics

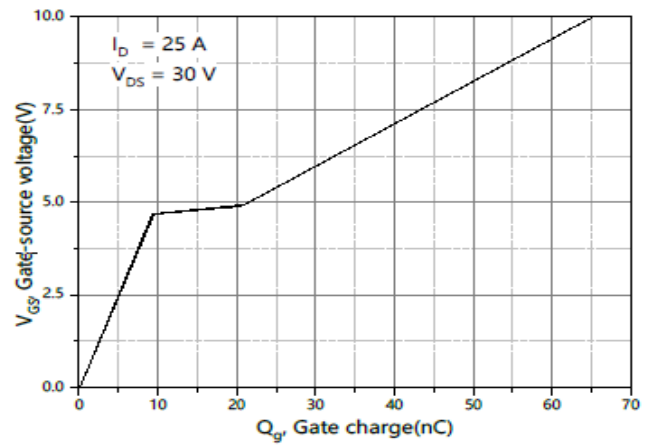


Figure4. Gate Charge

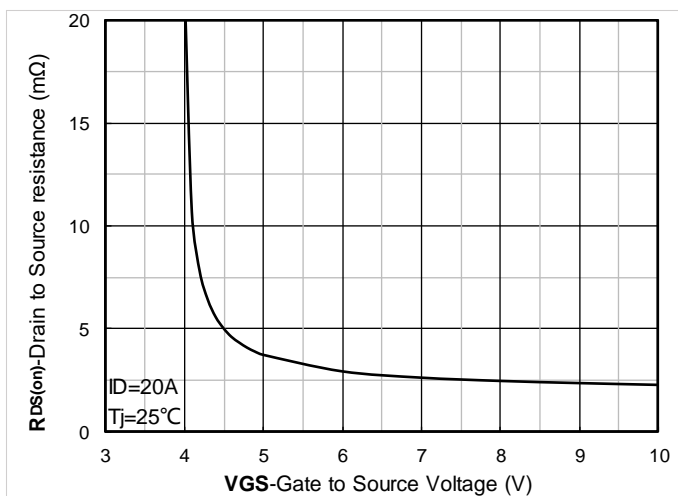


Figure 5. On-Resistance vs Gate to Source Voltage

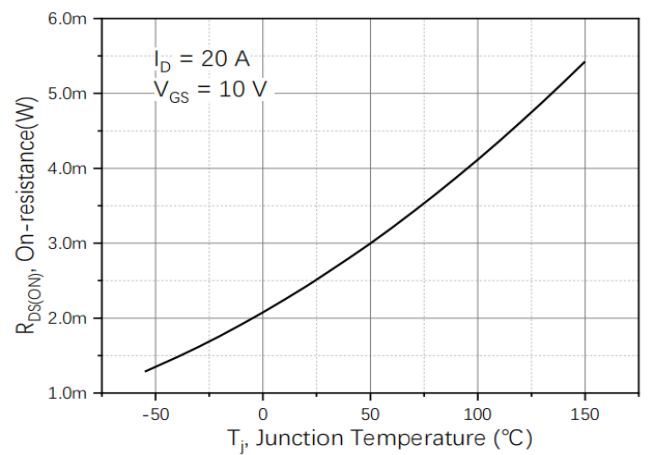


Figure 6. Drain-Source on Resistance

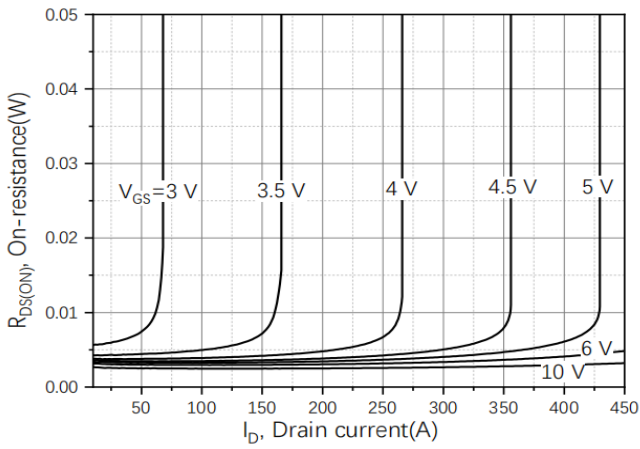


Figure 7. Drain-Source on Resistance

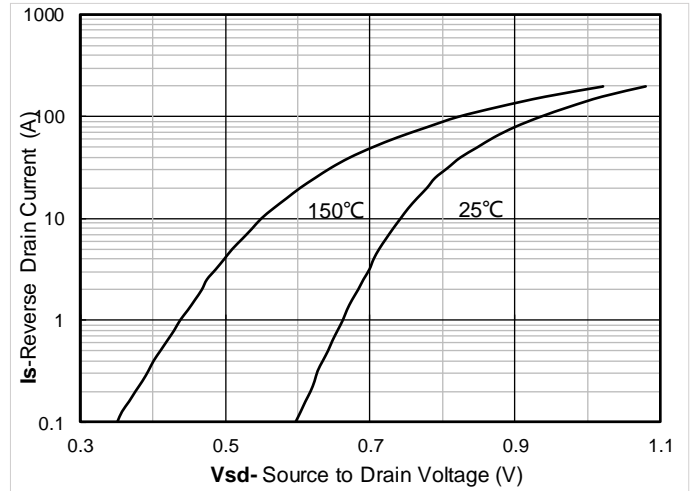


Figure 8. Forward characteristics of reverse diode

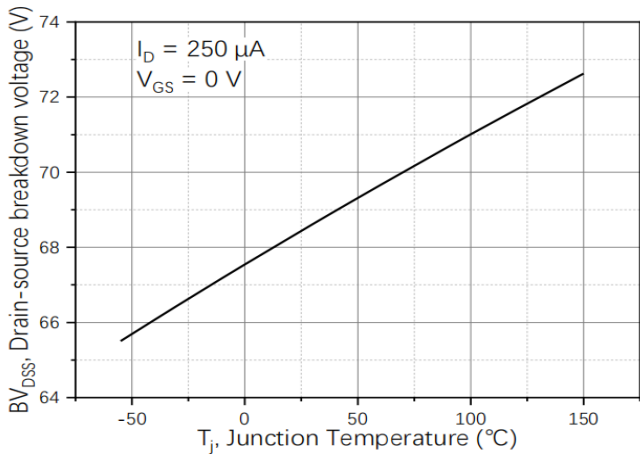


Figure 9. Drain-source breakdown voltage

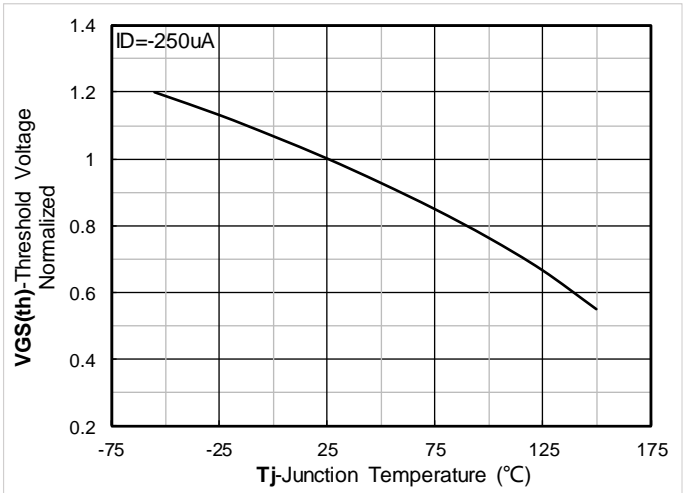


Figure 10. Normalized Threshold voltage

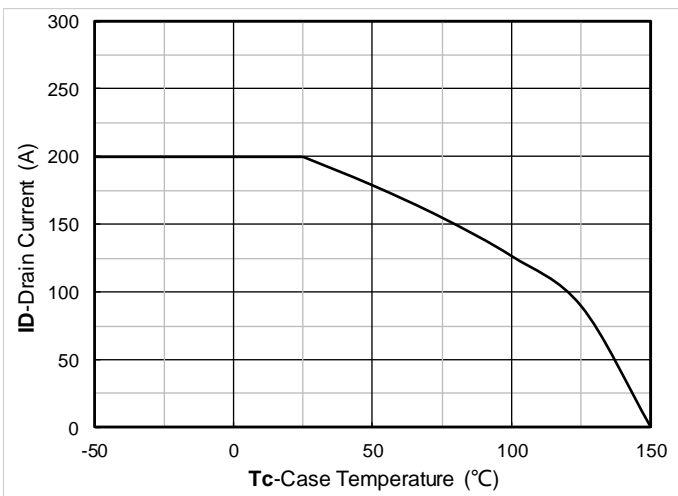


Figure 11. Current dissipation

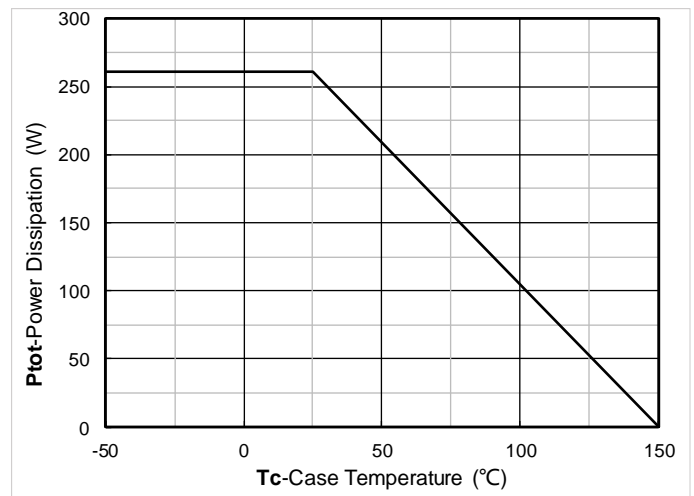


Figure 12. Power dissipation

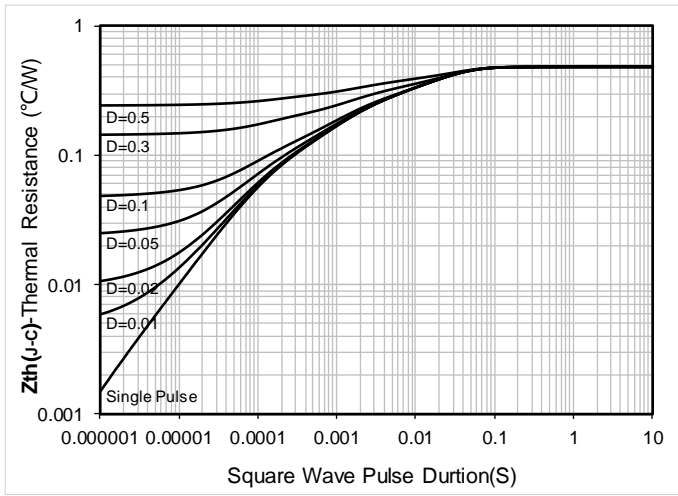


Figure 13. Maximum Transient Thermal Impedance

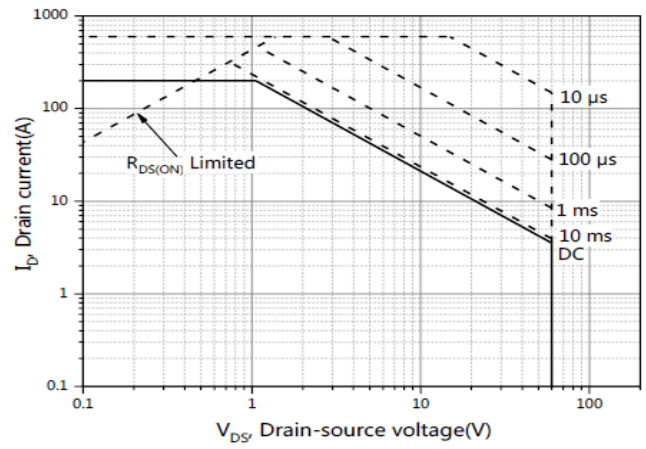


Figure 14. Safe Operation Area

## ■ Test circuits and waveforms

Figure A: Gate Charge Test Circuit & Waveforms

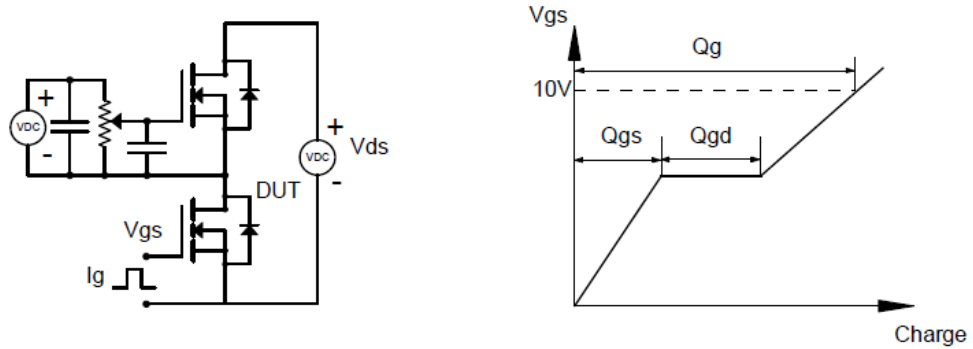


Figure B: Resistive Switching Test Circuit & Waveforms

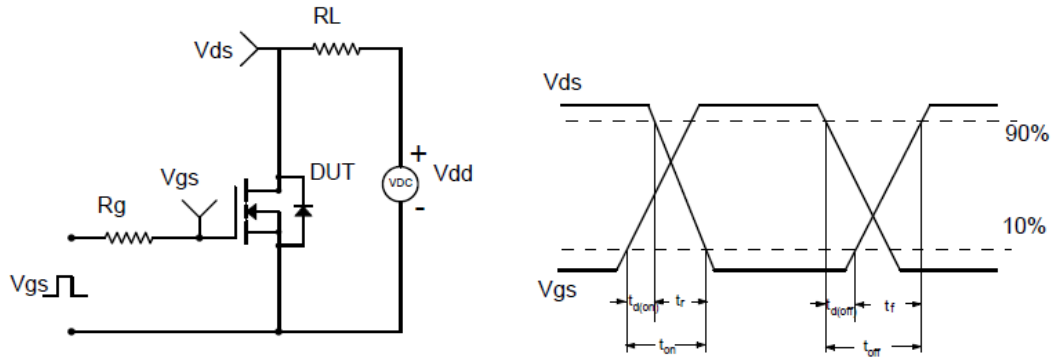


Figure C: Unclamped Inductive Switching (UIS) Test

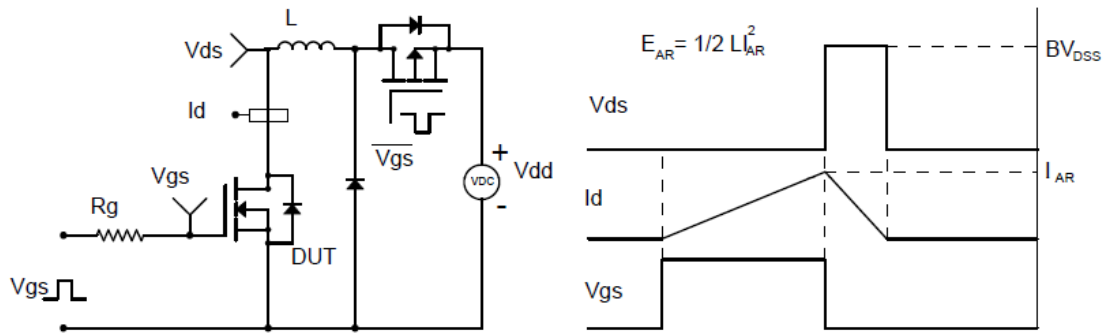
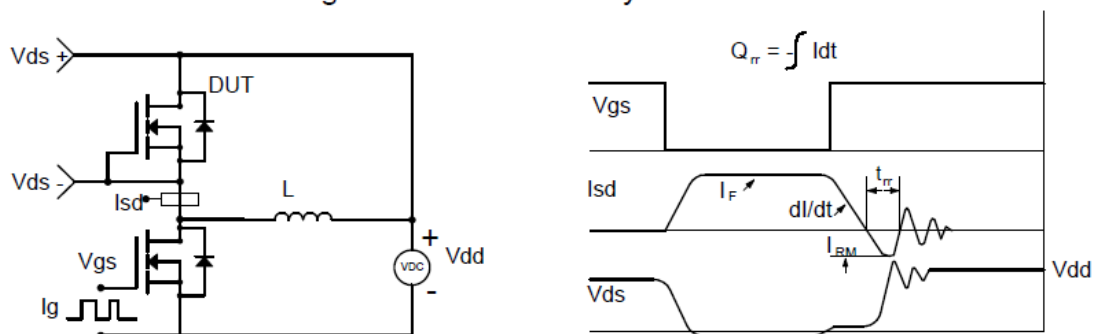
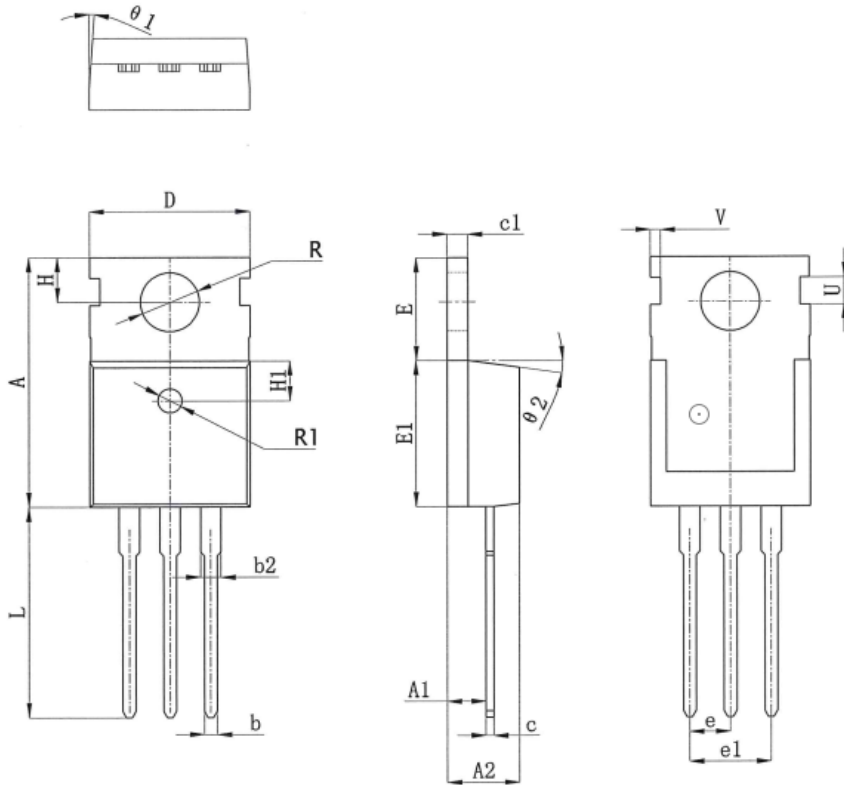


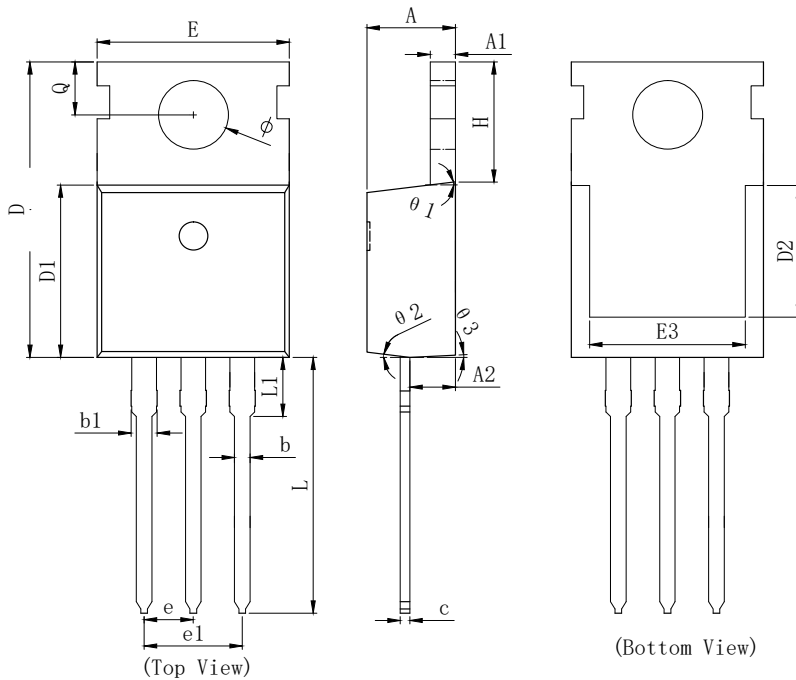
Figure D: Diode Recovery Test Circuit & Waveforms



# TO-220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.400	15.600	15.800
A1	2.350	2.400	2.500
A2	4.400	4.500	4.700
b	0.700	0.800	0.900
b2	1.180	1.310	1.440
c	0.480	0.500	0.560
c1	1.290	1.300	1.320
D	9.800	10.000	10.200
E	6.400	6.500	6.600
E1	9.000	9.100	9.200
e	2.420	2.540	2.660
e1	4.840	5.080	5.320
H	2.730	2.800	2.870
H1	2.400	2.500	2.600
L	13.020	13.370	13.720
R	3.500	3.600	3.730
R1	1.400	1.500	1.600
U	1.650	1.750	1.850
V	0.580	0.680	0.780
$\theta 1$	2°	2.5°	3°
$\theta 2$	6.5°	7°	7.5°



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
$\phi$	3.400	3.600	3.800
Q	2.600	2.800	3.000
$\theta 1$	7° TYP		
$\theta 2$	7° TYP		
$\theta 3$	3° TYP		


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